

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

TI-2000.1

Application Number

10/054,957

Applicant(s)

Theodore W. Houston et al.

Filing Date

10/25/02
Herewith

Group Art Unit

2822

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TMT		4,948,745	8/90	Pfiester et al.	437	41	
		5,532,175 5,532,175	7/96	Racanelli et al.	437	29	
		5,766,969	6/98	Fulford, Jr., et al.	437	44	
		5,804,497	9/98	Gardner et al.	438	529	
		5,858,848	1/99	Gardner et al.	438	305	
		6,228,725	5/01	Nandakumar et al.	438	289	
TMT		5,374,574	12/94	Kwon	437	44	

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FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

TMT		G.G. Shahidi et al. "Indium Channel Implant for Improved Short-Channel Behavior of Submicrometer NMOSFETs", IEEE 1993, pp 409-411

EXAMINER

T. Thomas

DATE CONSIDERED

02-09-03

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.